

Chi-Te Liang

List of Publications by Year in descending order

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238
papers

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docs citations

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times ranked

8887
citing authors

#	ARTICLE	IF	CITATIONS
1	Ultra-high-Gain Photodetectors Based on Atomically Thin Graphene-MoS ₂ Heterostructures. <i>Scientific Reports</i> , 2014, 4, 3826.	1.6	771
2	Wafer-scale MoS ₂ thin layers prepared by MoO ₃ sulfurization. <i>Nanoscale</i> , 2012, 4, 6637.	2.8	621
3	Nitrogen-Doped Graphene Sheets Grown by Chemical Vapor Deposition: Synthesis and Influence of Nitrogen Impurities on Carrier Transport. <i>ACS Nano</i> , 2013, 7, 6522-6532.	7.3	264
4	Synthesis of Graphene-ZnO-Au Nanocomposites for Efficient Photocatalytic Reduction of Nitrobenzene. <i>Environmental Science & Technology</i> , 2013, 47, 6688-6695.	4.6	204
5	Clean Lifting Transfer of Large Area Residual-Free Graphene Films. <i>Advanced Materials</i> , 2013, 25, 4521-4526.	11.1	157
6	Intermixing-seeded growth for high-performance planar heterojunction perovskite solar cells assisted by precursor-capped nanoparticles. <i>Energy and Environmental Science</i> , 2016, 9, 1282-1289.	15.6	157
7	Plant leaf-derived graphene quantum dots and applications for white LEDs. <i>New Journal of Chemistry</i> , 2014, 38, 4946-4951.	1.4	134
8	Extrinsic Origin of Persistent Photoconductivity in Monolayer MoS ₂ Field Effect Transistors. <i>Scientific Reports</i> , 2015, 5, 11472.	1.6	110
9	Photoluminescent graphene quantum dots for in vivo imaging of apoptotic cells. <i>Nanoscale</i> , 2015, 7, 2504-2510.	2.8	100
10	Electrical Polarization-Induced Ultrahigh Responsivity Photodetectors Based on Graphene and Graphene Quantum Dots. <i>Advanced Functional Materials</i> , 2016, 26, 620-628.	7.8	98
11	Thermoelectric signature of the excitation spectrum of a quantum dot. <i>Physical Review B</i> , 1997, 55, R10197-R10200.	1.1	97
12	Electroluminescence from ZnO/Si-Nanotips Light-Emitting Diodes. <i>Nano Letters</i> , 2009, 9, 1839-1843.	4.5	83
13	Detection of Coulomb Charging around an Antidot in the Quantum Hall Regime. <i>Physical Review Letters</i> , 1999, 83, 160-163.	2.9	67
14	Mechanism of giant enhancement of light emission from Au/CdSe nanocomposites. <i>Nanotechnology</i> , 2007, 18, 415707.	1.3	64
15	Synthesis of enzyme mimics of iron telluride nanorods for the detection of glucose. <i>Chemical Communications</i> , 2012, 48, 4079.	2.2	61
16	Low Carrier Density Epitaxial Graphene Devices On SiC. <i>Small</i> , 2015, 11, 90-95.	5.2	59
17	Spin-dependent transport in a quasiballistic quantum wire. <i>Physical Review B</i> , 2000, 61, 9952-9955.	1.1	51
18	Experimental Evidence for Coulomb Charging Effects in an Open Quantum Dot at Zero Magnetic Field. <i>Physical Review Letters</i> , 1998, 81, 3507-3510.	2.9	50

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19	Strong luminescence from strain relaxed InGaN/GaN nanotips for highly efficient light emitters. Optics Express, 2007, 15, 9357.	1.7	50
20	Ultrasensitive Gas Sensors Based on Vertical Graphene Nanowalls/SiC/Si Heterostructure. ACS Sensors, 2019, 4, 406-412.	4.0	46
21	Experimental evidence for Efros-Shklovskii variable range hopping in hydrogenated graphene. Solid State Communications, 2012, 152, 905-908.	0.9	45
22	Sunlight-activated graphene-heterostructure transparent cathodes: enabling high-performance n-graphene/p-Si Schottky junction photovoltaics. Energy and Environmental Science, 2015, 8, 2085-2092.	15.6	42
23	Cross-linked PMMA as a low-dimensional dielectric sacrificial layer. Journal of Microelectromechanical Systems, 2003, 12, 641-648.	1.7	41
24	Fabrication and transport properties of clean long one-dimensional quantum wires formed in modulation-doped GaAs/AlGaAs heterostructures. Applied Physics Letters, 1999, 75, 2975-2977.	1.5	37
25	Spin-dependent photocurrent induced by Rashba-type spin splitting in $\text{Al}_{0.25}\text{Ga}_{0.75}\text{N}/\text{GaN}$ heterostructures. Physical Review B, 2007, 75, .	1.1	36
26	Zero-field spin splitting in modulation-doped $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ two-dimensional electron systems. Applied Physics Letters, 2005, 86, 222102.	1.5	35
27	High-Performance InSe Transistors with Ohmic Contact Enabled by Nonrectifying Barrier-Type Indium Electrodes. ACS Applied Materials & Interfaces, 2018, 10, 33450-33456.	4.0	35
28	Multicolor Ultralow-Threshold Random Laser Assisted by Vertical Graphene Network. Advanced Optical Materials, 2018, 6, 1800382.	3.6	35
29	Effective mass of two-dimensional electron gas in an $\text{Al}_{0.2}\text{Ga}_{0.8}\text{N}/\text{GaN}$ heterojunction. Applied Physics Letters, 2001, 79, 66-68.	1.5	34
30	Transport in a gated $\text{Al}_{0.18}\text{Ga}_{0.82}\text{N}/\text{GaN}$ electron system. Journal of Applied Physics, 2003, 94, 3181-3184.	1.1	32
31	Exchange-enhanced g-factors in an $\text{Al}_{0.25}\text{Ga}_{0.75}\text{N}/\text{GaN}$ two-dimensional electron system. Journal of Applied Physics, 2004, 96, 7370-7373.	1.1	32
32	Magnesium Doping of In-rich InGaN. Japanese Journal of Applied Physics, 2007, 46, 2840-2843.	0.8	32
33	Ultrahigh contrast light valve driven by electrocapillarity of liquid gallium. Applied Physics Letters, 2009, 95, .	1.5	31
34	Growth and characterization of ZnO/ZnTe core/shell nanowire arrays on transparent conducting oxide glass substrates. Nanoscale Research Letters, 2012, 7, 401.	3.1	30
35	Characterization of Single-Crystalline Aluminum Thin Film on (100) GaAs Substrate. Japanese Journal of Applied Physics, 2013, 52, 045801.	0.8	30
36	Insulator-quantum Hall conductor transitions at low magnetic field. Physical Review B, 2001, 65, .	1.1	29

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37	Transport in disordered monolayer MoS ₂ nanoflakes—evidence for inhomogeneous charge transport. <i>Nanotechnology</i> , 2014, 25, 375201.	1.3	29
38	Resonant transmission through an open quantum dot. <i>Physical Review B</i> , 1997, 55, 6723-6726.	1.1	28
39	Fabrication and photoresponse of ZnO nanowires/CuO coaxial heterojunction. <i>Nanoscale Research Letters</i> , 2013, 8, 387.	3.1	28
40	Rational design of hetero-dimensional C-ZnO/MoS ₂ nanocomposite anchored on 3D mesoporous carbon framework towards synergistically enhanced stability and efficient visible-light-driven photocatalytic activity. <i>Chemosphere</i> , 2021, 266, 129148.	4.2	28
41	Transport behavior and negative magnetoresistance in chemically reduced graphene oxide nanofilms. <i>Nanotechnology</i> , 2011, 22, 335701.	1.3	27
42	Robust fractional quantum Hall effect in the N=2 Landau level in bilayer graphene. <i>Nature Communications</i> , 2016, 7, 13908.	5.8	27
43	Electron transport in In-rich In _x Ga _{1-x} films. <i>Journal of Applied Physics</i> , 2005, 97, 046101.	1.1	26
44	From localization to Landau quantization in a two-dimensional GaAs electron system containing self-assembled InAs quantum dots. <i>Physical Review B</i> , 2004, 69, .	1.1	25
45	Fe ₂ O ₃ /Al ₂ O ₃ microboxes for efficient removal of heavy metal ions. <i>New Journal of Chemistry</i> , 2017, 41, 7751-7757.	1.4	25
46	Room-temperature violet luminescence and ultraviolet photodetection of Sb-doped ZnO/Al-doped ZnO homojunction array. <i>Nanoscale Research Letters</i> , 2013, 8, 313.	3.1	24
47	Spin-orbit-coupled superconductivity. <i>Scientific Reports</i> , 2014, 4, 5438.	1.6	22
48	Epitaxial growth of Bi ₂ Te ₃ topological insulator thin films by temperature-gradient induced physical vapor deposition (PVD). <i>Journal of Alloys and Compounds</i> , 2016, 686, 989-997.	2.8	22
49	Spin-dependent transport in a clean one-dimensional channel. <i>Physical Review B</i> , 1999, 60, 10687-10690.	1.1	21
50	Electrically detected and microwave-modulated Shubnikov–de Haas oscillations in an Al _{0.4} Ga _{0.6} N/GaN heterostructure. <i>Journal of Applied Physics</i> , 2003, 93, 2055-2058.	1.1	21
51	A study on the epitaxial Bi ₂ Se ₃ thin film grown by vapor phase epitaxy. <i>AIP Advances</i> , 2016, 6, .	0.6	20
52	2D CTAB-MoSe ₂ Nanosheets and OD MoSe ₂ Quantum Dots: Facile Top-Down Preparations and Their Peroxidase-Like Catalytic Activity for Colorimetric Detection of Hydrogen Peroxide. <i>Nanomaterials</i> , 2020, 10, 2045.	1.9	20
53	Graphene quantum Hall effect parallel resistance arrays. <i>Physical Review B</i> , 2021, 103, .	1.1	20
54	Atypical quantized resistances in millimeter-scale epitaxial graphene p-n junctions. <i>Carbon</i> , 2019, 154, 230-237.	5.4	19

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55	Unprecedented random lasing in 2D organolead halide single-crystalline perovskite microrods. <i>Nanoscale</i> , 2020, 12, 18269-18277.	2.8	19
56	Effect of nitrogen contents on the temperature dependence of photoluminescence in InGaAsN ^x /GaAs single quantum wells. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006, 24, 1223-1227.	0.9	17
57	Coulomb charging effects in an open quantum dot device. <i>Journal of Physics Condensed Matter</i> , 2001, 13, 9515-9534.	0.7	16
58	Chemical-doping-driven crossover from graphene to "ordinary metal" in epitaxial graphene grown on SiC. <i>Nanoscale</i> , 2017, 9, 11537-11544.	2.8	16
59	On the low-field insulator-quantum Hall conductor transitions. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 240-243.	1.3	15
60	Design Optimization for Maximized Thermoelectric Generator Performance. <i>Journal of Electronic Materials</i> , 2020, 49, 306-310.	1.0	15
61	Multilayered gated lateral quantum dot devices. <i>Applied Physics Letters</i> , 2000, 76, 1134-1136.	1.5	14
62	Substrate dependence of large ordinary magnetoresistance in sputtered Bi films. <i>Journal of Magnetism and Magnetic Materials</i> , 2004, 272-276, 1769-1771.	1.0	14
63	Huge positive magnetoresistance in an InN film. <i>Applied Physics Letters</i> , 2007, 90, 172101.	1.5	14
64	Optical characteristics of nonpolar-plane ZnO thin film on (010) LiGaO ₂ substrate. <i>Semiconductor Science and Technology</i> , 2014, 29, 085004.	1.0	14
65	Linear magnetoresistance in monolayer epitaxial graphene grown on SiC. <i>Materials Letters</i> , 2016, 174, 118-121.	1.3	14
66	Theory of the quantum Hall effect in finite graphene devices. <i>Physical Review B</i> , 2010, 81, .	1.1	13
67	Atomic-scale epitaxial aluminum film on GaAs substrate. <i>AIP Advances</i> , 2017, 7, 075213.	0.6	13
68	Highly sensitive broadband binary photoresponse in gateless epitaxial graphene on 4H-SiC. <i>Carbon</i> , 2021, 184, 72-81.	5.4	13
69	Ferroelectric 2D ice under graphene confinement. <i>Nature Communications</i> , 2021, 12, 6291.	5.8	13
70	Measurements of a composite fermion split-gate device. <i>Physical Review B</i> , 1996, 53, R7596-R7598.	1.1	12
71	A study on the universality of the magnetic-field-induced phase transitions in the two-dimensional electron system in an AlGaAs/GaAs heterostructure. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 232-235.	1.3	12
72	Huge positive magnetoresistance of GaAs ^x /AlGaAs high electron mobility transistor structures at high temperatures. <i>Applied Physics Letters</i> , 2007, 90, 252106.	1.5	12

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73	Efficient reduction of graphene oxide catalyzed by copper. <i>Physical Chemistry Chemical Physics</i> , 2012, 14, 3083.	1.3	12
74	Mesoscopic conductance fluctuations in multi-layer graphene. <i>Applied Physics Letters</i> , 2013, 103, 043117.	1.5	12
75	Insulator-quantum Hall transition in monolayer epitaxial graphene. <i>RSC Advances</i> , 2016, 6, 71977-71982.	1.7	12
76	Large, non-saturating magnetoresistance in single layer chemical vapor deposition graphene with an h-BN capping layer. <i>Carbon</i> , 2018, 136, 211-216.	5.4	12
77	Tunnelling transmission resonances through a zero-dimensional structure. <i>Semiconductor Science and Technology</i> , 1997, 12, 875-880.	1.0	11
78	Temperature-dependent optical properties of single quantum well with high nitrogen content for application grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2006, 291, 27-33.	0.7	11
79	From insulator to quantum Hall liquid at low magnetic fields. <i>Physical Review B</i> , 2008, 78, .	1.1	11
80	Evidence for formation of multi-quantum dots in hydrogenated graphene. <i>Nanoscale Research Letters</i> , 2012, 7, 459.	3.1	11
81	Weak localization and universal conductance fluctuations in multi-layer graphene. <i>Current Applied Physics</i> , 2014, 14, 108-111.	1.1	11
82	Electron-electron interactions in Al _{0.15} Ga _{0.85} N ⁺ GaN high electron mobility transistor structures grown on Si substrates. <i>Applied Physics Letters</i> , 2007, 90, 022107.	1.5	10
83	Non-ohmic behavior of carrier transport in highly disordered graphene. <i>Nanotechnology</i> , 2013, 24, 165201.	1.3	10
84	Green synthesis of Si ⁺ GQD nanocomposites as cost-effective catalysts for oxygen reduction reaction. <i>RSC Advances</i> , 2016, 6, 108941-108947.	1.7	10
85	Temperature dependence of electron density and electron ⁺ electron interactions in monolayer epitaxial graphene grown on SiC. <i>2D Materials</i> , 2017, 4, 025007.	2.0	10
86	Weak localization and electron-electron interactions in a two-dimensional grid lateral surface superlattice. <i>Physical Review B</i> , 1994, 49, 8518-8521.	1.1	9
87	One-dimensional ballistic channel with a triple-barrier longitudinal potential: Measurement and model. <i>Physical Review B</i> , 1994, 49, 14078-14080.	1.1	9
88	Transport properties of two-dimensional electron gases containing linear ordering InAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 2001, 78, 3896-3898.	1.5	9
89	Gradual decrease of conductance of an adiabatic ballistic constriction below $2e^2\hbar$. <i>Physical Review B</i> , 2004, 70, .	1.1	9
90	Superconductivity and mixed-state characteristic of InN films by metal-organic vapor phase epitaxy. <i>Diamond and Related Materials</i> , 2006, 15, 1179-1183.	1.8	9

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91	An experimental study on $\nu(2)$ modular symmetry in the quantum Hall system with a small spin splitting. Journal of Physics Condensed Matter, 2007, 19, 026205.	0.7	9
92	Probing Landau quantization with the presence of insulator-quantum Hall transition in a GaAs two-dimensional electron system. Journal of Physics Condensed Matter, 2008, 20, 295223.	0.7	9
93	The Growth and Characterization of ZnO/ZnTe Core-Shell Nanowires and the Electrical Properties of ZnO/ZnTe Core-Shell Nanowire Field Effect Transistor. Journal of Nanoscience and Nanotechnology, 2011, 11, 2042-2046.	0.9	9
94	On the direct insulator-quantum Hall transition in two-dimensional electron systems in the vicinity of nanoscaled scatterers. Nanoscale Research Letters, 2011, 6, 131.	3.1	9
95	A delta-doped quantum well system with additional modulation doping. Nanoscale Research Letters, 2011, 6, 139.	3.1	9
96	Experimental evidence for direct insulator-quantum Hall transition in multi-layer graphene. Nanoscale Research Letters, 2013, 8, 214.	3.1	9
97	Spin polarization in a two-dimensional electron gas in GaAs. Physica Scripta, 2013, 87, 045703.	1.2	9
98	Dirac fermion heating, current scaling, and direct insulator-quantum Hall transition in multilayer epitaxial graphene. Nanoscale Research Letters, 2013, 8, 360.	3.1	9
99	Intrinsic magnetic properties of plant leaf-derived graphene quantum dots. Materials Letters, 2016, 170, 110-113.	1.3	9
100	Demonstration of Rashba spin splitting in an Al _{0.25} Ga _{0.75} N/GaN heterostructure by microwave-modulated Shubnikov-de Haas oscillations. Semiconductor Science and Technology, 2007, 22, 870-874.	1.0	8
101	Direct deposition of single-walled carbon nanotube thin films via electrostatic spray assisted chemical vapor deposition. Nanotechnology, 2009, 20, 065601.	1.3	8
102	Chiral angle dependence of resonance window widths in (2n+m) families of single-walled carbon nanotubes. Applied Physics Letters, 2010, 96, .	1.5	8
103	Iron telluride nanorods-based system for the detection of total mercury in blood. Journal of Hazardous Materials, 2012, 243, 286-291.	6.5	8
104	Pure electron-electron dephasing in percolative aluminum ultrathin film grown by molecular beam epitaxy. Nanoscale Research Letters, 2015, 10, 71.	3.1	8
105	Variable range hopping and nonlinear transport in monolayer epitaxial graphene grown on SiC. Semiconductor Science and Technology, 2016, 31, 105008.	1.0	8
106	Crossover from Efros-Shklovskii to Mott variable range hopping in monolayer epitaxial graphene grown on SiC. Chinese Journal of Physics, 2017, 55, 1235-1241.	2.0	8
107	Conductance interference effects in an electron-beam-resist-free chemical vapor deposition graphene device sandwiched between two h-BN sheets. Carbon, 2019, 154, 238-243.	5.4	8
108	Large transconductance oscillations in a single-well vertical Aharonov-Bohm interferometer. Physical Review B, 2000, 62, R10630-R10632.	1.1	7

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109	Effects of Zeeman spin splitting on the modular symmetry in the quantum Hall effect. <i>Microelectronics Journal</i> , 2005, 36, 469-471.	1.1	7
110	Influence of the incorporation of metals on the optical properties of MCM-41. <i>Journal of Luminescence</i> , 2008, 128, 553-558.	1.5	7
111	Crossover from negative to positive magnetoresistance in a Si delta-doped GaAs single quantum well. <i>Solid State Communications</i> , 2010, 150, 1104-1107.	0.9	7
112	Controllable Disorder in a Hybrid Nanoelectronic System: Realization of a Superconducting Diode. <i>Scientific Reports</i> , 2013, 3, 2274.	1.6	7
113	Magnetotransport in variable-coupling one-dimensional ballistic constrictions. <i>Journal of Applied Physics</i> , 2002, 92, 5304-5309.	1.1	6
114	Transport and quantum lifetime dependence on electron density in gated GaAs/AlGaAs heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 312-315.	1.3	6
115	Growth and characterization of GaN/AlGaIn high-electron mobility transistors grown on p-type Si substrates. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 32, 566-568.	1.3	6
116	Electron heating and huge positive magnetoresistance in an AlGaAs ⁺ GaAs high electron mobility transistor structure at high temperatures. <i>Applied Physics Letters</i> , 2008, 92, 152117.	1.5	6
117	Probing two-dimensional metallic-like and localization effects at low magnetic fields. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 1142-1144.	1.3	6
118	Probing the onset of strong localization and electron-electron interactions with the presence of a direct insulator-quantum Hall transition. <i>Solid State Communications</i> , 2010, 150, 1902-1905.	0.9	6
119	Proposed Nonmagnetic Stern-Gerlach Experiment Using Electron Diffraction. <i>Physical Review Letters</i> , 2010, 105, 217205.	2.9	6
120	Electron-electron interaction in high-quality epitaxial graphene. <i>New Journal of Physics</i> , 2011, 13, 113005.	1.2	6
121	Application of Impedance Measurement Technology in Distinguishing Different Tea Samples with Ppy/SWCNT Composite Sensing Material. <i>Journal of the Chinese Chemical Society</i> , 2011, 58, 714-722.	0.8	6
122	Probing temperature-driven flow lines in a gated two-dimensional electron gas with tunable spin-splitting. <i>Journal of Physics Condensed Matter</i> , 2012, 24, 405801.	0.7	6
123	Electron transport in a GaPSb film. <i>Nanoscale Research Letters</i> , 2012, 7, 640.	3.1	6
124	Probing weak localization in chemical vapor deposition graphene wide constriction using scanning gate microscopy. <i>Nanotechnology</i> , 2016, 27, 075601.	1.3	6
125	Accessing ratios of quantized resistances in graphene p-n junction devices using multiple terminals. <i>AIP Advances</i> , 2020, 10, 025112.	0.6	6
126	Two-dimensional molybdenum trioxide nanoflakes wrapped with interlayer-expanded molybdenum disulfide nanosheets: Superior performances in supercapacitive energy storage and visible-light-driven photocatalysis. <i>International Journal of Hydrogen Energy</i> , 2021, 46, 34663-34678.	3.8	6

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127	Measurements of a composite fermion split-gate. Surface Science, 1996, 361-362, 71-74.	0.8	5
128	Al _{0.15} Ga _{0.85} N ^δ -GaN high electron mobility transistor structures grown on p-type Si substrates. Applied Physics Letters, 2006, 89, 132107.	1.5	5
129	Optical investigation of an AlGaIn/GaN interface with the presence of a two-dimensional electron gas. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 43, 125-129.	1.3	5
130	Ballistic Transport in 1D GaAs/AlGaAs Heterostructures. , 2011, , 279-325.		5
131	Insulator, semiclassical oscillations and quantum Hall liquids at low magnetic fields. Journal of Physics Condensed Matter, 2012, 24, 405601.	0.7	5
132	Size effects on phonon localization and Raman enhancement in silicon nanotips. Journal of Raman Spectroscopy, 2013, 44, 81-85.	1.2	5
133	Observation of quantum Hall plateau-plateau transition and scaling behavior of the zeroth Landau level in graphene<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>p</mml:mi><mml:mtext>âˆ²</mml:mtext><mml:mi>n</mml:mi></mml:mrow></mml:math>	1.1	5
134	Experimental Evidence for Weak Insulator-Quantum Hall Transitions in GaN/AlGaIn Two-Dimensional Electron Systems. Journal of the Korean Physical Society, 2007, 50, 1643.	0.3	5
135	Electron Heating and Current Scaling in a GaAs Two-Dimensional Electron System. Journal of the Korean Physical Society, 2007, 50, 1662.	0.3	5
136	Phase Modulation of Self-Gating in Ionic Liquid-Functionalized InSe Field-Effect Transistors. Nano Letters, 2022, 22, 2270-2276.	4.5	5
137	Ballistic composite fermions in semiconductor nanostructures. Physical Review B, 1996, 53, 9602-9605.	1.1	4
138	Exchange-enhanced LandÄ© g-factor, effective disorder and collapse of spin-splitting in a two-dimensional GaAs electron system. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 424-427.	1.3	4
139	Effect of Buffer Layers on Electrical, Optical and Structural Properties of AlGaIn/GaN Heterostructures Grown on Si. Japanese Journal of Applied Physics, 2006, 45, 2516-2518.	0.8	4
140	Tunable insulator-quantum Hall transition in a weakly interacting two-dimensional electron system. Nanoscale Research Letters, 2013, 8, 307.	3.1	4
141	Hot carriers in epitaxial graphene sheets with and without hydrogen intercalation: role of substrate coupling. Nanoscale, 2014, 6, 10562-10568.	2.8	4
142	Imaging coherent transport in chemical vapor deposition graphene wide constriction by scanning gate microscopy. Applied Physics Letters, 2016, 108, .	1.5	4
143	Modulation of spin-charge conversion in silicon. Applied Physics Letters, 2019, 115, 232101.	1.5	4
144	A Self-Assembled Graphene Ribbon Device on SiC. ACS Applied Electronic Materials, 2020, 2, 204-212.	2.0	4

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145	Disorder-induced 2D superconductivity in a NbTiN film grown on Si by ultrahigh-vacuum magnetron sputtering. <i>Superconductor Science and Technology</i> , 2022, 35, 064003.	1.8	4
146	Dynamics of transient hole doping in epitaxial graphene. <i>Physical Review B</i> , 2022, 105, .	1.1	4
147	Reflection of edge states in the fractional quantum Hall regime. <i>Solid State Communications</i> , 1995, 96, 327-331.	0.9	3
148	Experimental evidence of a metal-insulator transition in a half-filled Landau level. <i>Solid State Communications</i> , 1997, 102, 327-330.	0.9	3
149	Evidence for charging effects in an open dot at zero magnetic field. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 418-422.	1.3	3
150	Detection of Coulomb charging around an antidot. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 495-498.	1.3	3
151	Quantum magneto-transport in two-dimensional GaAs electron gases and SiGe hole gases. <i>Journal of Physics and Chemistry of Solids</i> , 2001, 62, 1789-1796.	1.9	3
152	Coulomb oscillations of the ballistic conductance in a quasi-one-dimensional quantum dot. <i>JETP Letters</i> , 2001, 74, 209-212.	0.4	3
153	Spin-dependent transport in a dilute two-dimensional GaAs electron gas in a parallel magnetic field. <i>Physical Review B</i> , 2001, 64, .	1.1	3
154	Insulator-quantum Hall transitions in two-dimensional electron gas containing self-assembled InAs dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 17, 292-293.	1.3	3
155	Spin-dependent transport in a dilute two-dimensional GaAs electron gas in an in-plane magnetic field. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 18, 141-142.	1.3	3
156	Experimental evidence for screening effects from surface states in GaAs/AlGaAs based nanostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 570-573.	1.3	3
157	Experimental evidence for Drude-Boltzmann-like transport in a two-dimensional electron gas in an AlGaIn/GaN heterostructure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1713-1716.	0.8	3
158	Effect of the electromagnetic environment on the dynamics of charge and phase particles in one-dimensional arrays of small Josephson junctions. <i>Europhysics Letters</i> , 2011, 96, 47004.	0.7	3
159	Direct measurement of the spin gaps in a gated GaAs two-dimensional electron gas. <i>Nanoscale Research Letters</i> , 2013, 8, 138.	3.1	3
160	Non-monotonic magnetoresistivity in two-dimensional electron systems. <i>Journal of the Korean Physical Society</i> , 2014, 65, 1503-1507.	0.3	3
161	Localization and electron-electron interactions in few-layer epitaxial graphene. <i>Nanotechnology</i> , 2014, 25, 245201.	1.3	3
162	Hot Carriers in CVD-Grown Graphene Device with a Top h-BN Layer. <i>Journal of Nanomaterials</i> , 2018, 2018, 1-7.	1.5	3

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163	Spin Hall angle and spin diffusion length of permalloy. AIP Advances, 2020, 10, .	0.6	3
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